# EVQ1923-RE-00A



100V, 8A, High-Frequency Half-Bridge Gate Driver Evaluation Board

#### **DESCRIPTION**

The EVQ1923-RE-00A is an evaluation board designed to demonstrate the MPQ1923, a high-frequency half-bridge gate driver. The MPQ1923 has a 7A source current ( $I_{SOURCE}$ ) and 8A sink current ( $I_{SINK}$ ) at a 12V driver power supply voltage ( $V_{DD}$ ).

The integrated bootstrap (BST) diode reduces the external component count. The device's high-side MOSFET (HS-FET) and low-side MOSFET (LS-FET) drivers are controlled independently, and can be matched with a time delay (<5ns). If the IC supply is insufficient, then under-voltage lockout (UVLO) protection on both the HS-FET and LS-FET force the outputs low.

The MPQ1923 is designed for motor drivers and other power-control applications (e.g. telecommunication half-bridge power supplies, avionics DC/DC converters, two-switch forward converters, and active-clamp forward converters.

The MPQ1923 is available in a small QFN-10 (4mmx4mm) or QFN-8 (4mmx4mm) package.

The EVQ1923-RE-00A is configured as a buck converter. The INH and INL pins are independent signals. Choose complementary pulse-width modulation (PWM) signals and a proper dead time (DT) for INH and INL.

#### PERFORMANCE SUMMARY

Specifications are at  $T_A = 25$ °C, unless otherwise noted.

Parameters	Conditions	Value
Driver power supply voltage range (V <sub>DD</sub> )		5V to 17V
Input power supply voltage range (V <sub>IN</sub> )		0V to 100V
Floating HS-FET gate driver maximum source current (Isource_MAX)	V <sub>DD</sub> = 12V	7A
Floating HS-FET gate driver maximum sink current (Isink_MAX)	V <sub>DD</sub> = 12V	8A
LS-FET gate driver Isource_max	V <sub>DD</sub> = 12V	7A
LS-FET gate driver Isink_max	V <sub>DD</sub> = 12V	8A



### **EVQ1923-RE-00A EVALUATION BOARD**



LxWxH (10cmx10cmx3.8cm)

<b>Board Number</b>	MPS IC Number		
EVQ1923-RE-00A	MPQ1923GRE-AEC1		



#### **QUICK START GUIDE**

- 1. Preset the driver power supply between 5V and 17V.
- 2. Preset the input voltage (V<sub>IN</sub>) between 0V and 100V.
- 3. Connect two complementary pulse-width modulation (PWM) signals with a proper dead time to CN1. It is recommended to choose either 3.3V or 5V for the INH and INL logic high voltage.
- 4. Connect the driver power supply terminals to:
  - a. Positive (+): VDD
  - b. Negative (-): GND
- 5. Connect the input power supply terminals to:
  - a. Positive (+): V<sub>POWER</sub>
  - b. Negative (-): GND
- 6. Attach the load terminals to:
  - a. Positive (+): V<sub>LOAD</sub>
  - b. Negative (-): GND
- 7. Turn on the driver's power supply.
- 8. Check the INH, INL, DRVH, and DRVL signals to ensure that a sufficient dead time (DT) has been established for DRVH and DRVL.
- 9. Turn on the input power supply. The board should start up automatically.
- 10. Turn on the load, then check the output voltage (V<sub>OUT</sub>) and output current (I<sub>OUT</sub>) to ensure the buck circuitry is operating normally.
- 11. To turn off the system, follow the steps below:
  - a. Turn off the load.
  - b. Turn off the input power supply.
  - c. Turn off the driver power supply.

3

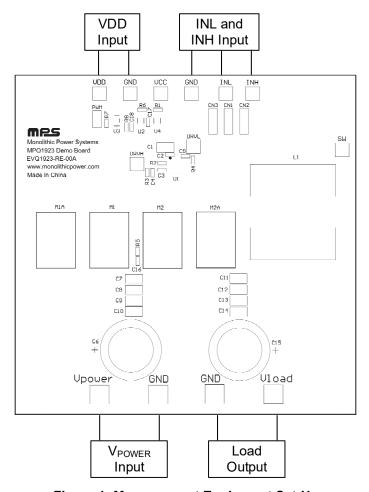


Figure 1: Measurement Equipment Set-Up



### **EVALUATION BOARD SCHEMATIC**

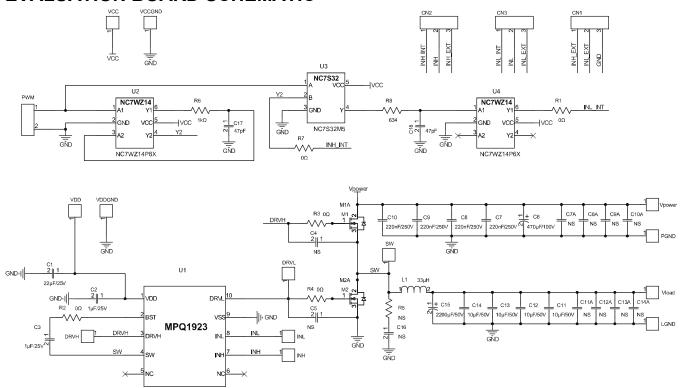


Figure 2: Evaluation Board Schematic



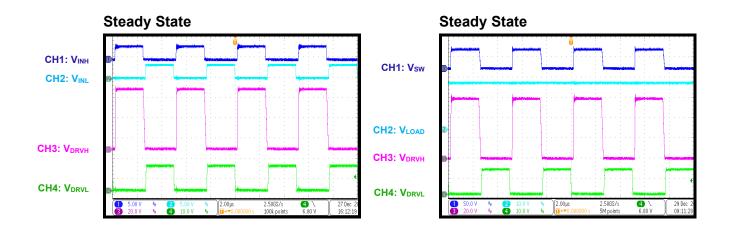
### **EVQ1923-RE-00A BILL OF MATERIALS**

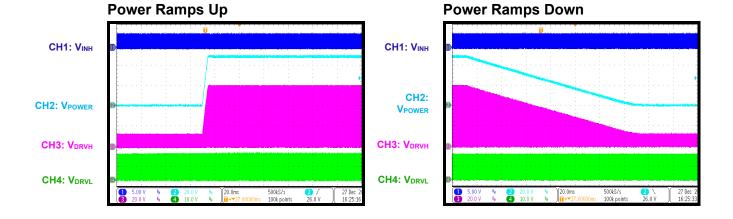
Qty	Ref	Value	Description	Package	Manufacturer	Manufacturer PN
1	C1	22µF	Ceramic capacitor, 25V, X7R	1210	Murata	GRM32ER71E22 6KE15L
2	C2, C3	1µF	Ceramic capacitor, 25V, X7R	0603	Murata	GCM188R71E10 5KA64D
2	C4, C5	NS				
1	C6	470µF	Electrolytic capacitor, 100V	DIP	Jianghai	CD263-100V470
4	C7, C8, C9, C10	220nF	Ceramic capacitor, 250V, X7R	1210	Murata	GRM32DR72E22 4KW01L
4	C11, C12, C13, C14	10μF	Ceramic capacitor, 50V, X7R	1210	Murata	GRM32ER71H10 6KA12L
9	C7A, C8A, C9A, C10A, C11A, C12A, C13A, C14A, C16	NS				
1	C15	2200µF	Electrolytic capacitor, 50V	DIP	Jianghai	CD28L-50V2200
3	R2, R3, R4	Ω0	Film resistor, 1%	0603	Yageo	RC0603FR- 070RL
1	R5	NS				
2	M1, M2	150V	N-channel MOSFET, 90A	TO-263	Analog Power	AMIB075N15N3- T1-PF
2	M1A, M2A	NS				
1	L1	33µH	Inductor, 33µH, 15.4A	SMD	Wurth	74437529203330
4	V <sub>POWER</sub> , V <sub>LOAD</sub> , GNDx2	2mm	Golden pin	SIP	Custom	
9	VDD, GND, VCC, GND, INL, INH, DRVH, DRVL, SW	1mm	Golden pin	SIP	Custom	
1	U1	MPQ1923	Half-bridge gate driver, 100V, 8A	QFN-10 (4mmx 4mm)	MPS	MPQ1923GRE- AEC1



#### **EVB TEST RESULTS**

 $V_{\text{DD}}$  = 12V,  $V_{\text{POWER}}$  = 48V, INH/INL = 200kHz, dead time = 200ns,  $I_{\text{LOAD}}$  = 1A,  $T_{\text{A}}$  = 25°C, unless otherwise noted.





### **PCB LAYOUT**

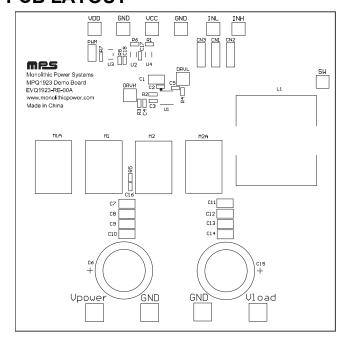


Figure 3: Top Silk

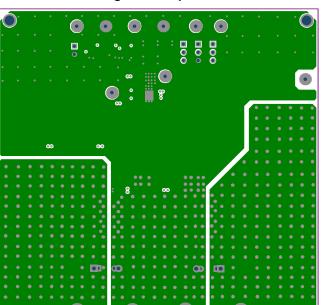


Figure 4: Top Layer

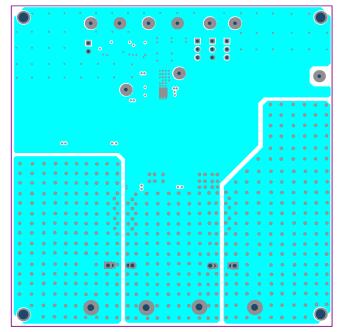
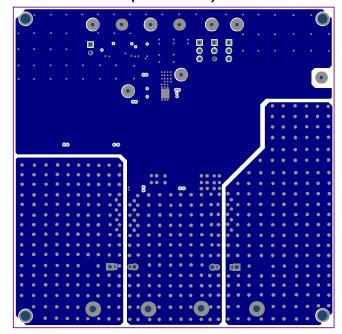


Figure 5: Mid-Layer 1

Figure 6: Mid-Layer 2

## **PCB LAYOUT** (continued)



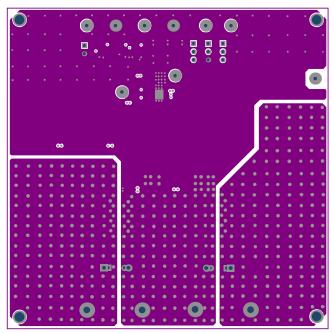
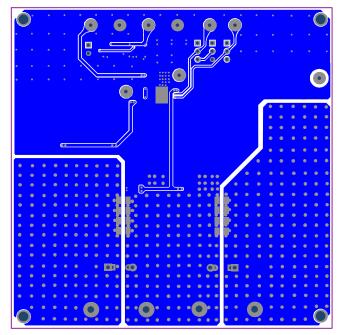


Figure 7: Mid-Layer 3

Figure 8: Mid-Layer 4



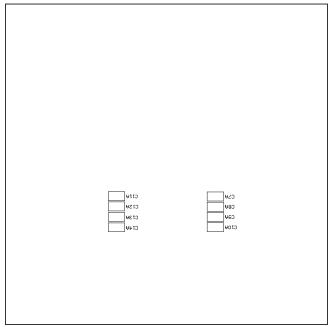


Figure 9: Bottom Layer

Figure 10: Bottom Silk